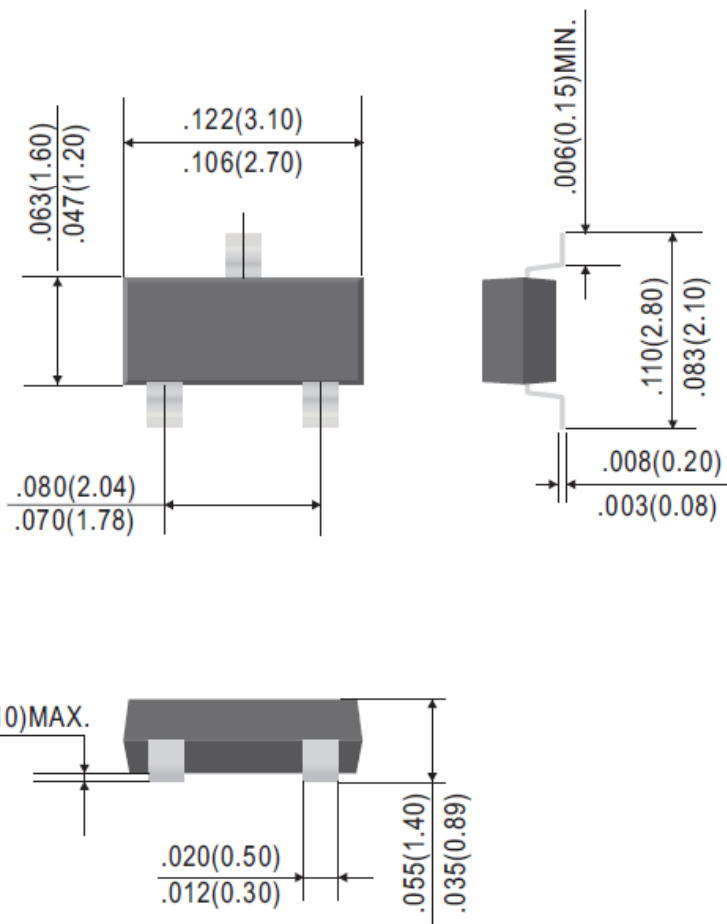
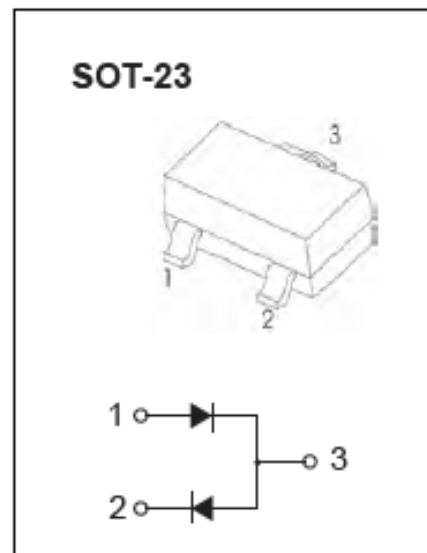




Dimensions in inches and (millimeters)



SWITCHING DIODE

FEATURES

- MMBD2004S type is a silicon switching dual in series diode
- Manufactured by the epitaxial planar process
- Designed for applications requiring high voltage capability, power dissipation
- Pb-Free package is available
- RoHS product for packing code suffix "G"
- Halogen free product for packing code suffix "H"
- Moisture Sensitivity Level 1

MARKING: B6D

Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)			
Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	300	V
DC Blocking Voltage	V_R	240	V
Peak Repetitive Current	I_O	200	mA
Continuous Forward Current	I_F	225	mA
Peak Repetitive Forward Current	I_{FRM}	625	mA
Forward Surge Current $t = 1\mu\text{s}$	I_{FSM}	4	A
Forward Surge Current $t = 1\text{s}$	I_{FSM}	1	A
Power Dissipation	P_D	250	mW
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Operating/ Storage Temperature Range	T_{STG}	-55~+150	$^{\circ}\text{C}$

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)					
Parameter	Symbol	Test conditions	Min.	Max.	Unit
Reverse Breakdown Voltage	$V_{(BR)}$	$I_R = 100\mu\text{A}$	240	—	V
Reverse Voltage Leakage Current	I_R	$V_R = 240\text{V}$	—	0.1	μA
Forward Voltage	V_F	$I_F = 100\text{mA}$	—	1	V
Diode Capacitance	C_T	$V_R = 0\text{V}$, $f = 1\text{MHz}$	—	5	pF
Revers Recovery Time	t_{rr}	$I_F = I_R = 30\text{mA}$, $R_L = 100\Omega$	—	50	ns